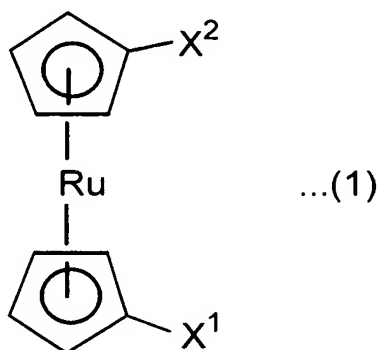


IN THE CLAIMS

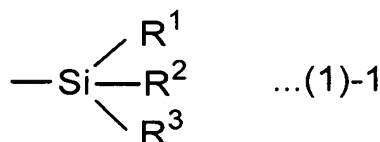
Please amend the claims as follows:

Claim 1 (Currently Amended): A ruthenium compound for chemical vapor deposition, ~~which is comprising~~ at least one compound selected from the group consisting of:

a compound represented by the following formula (1):



wherein X^1 and X^2 are each independently a ~~hydrogen atom~~, fluorine atom, trifluoromethyl group, pentafluoroethyl group or group represented by the following formula (1)-1:



wherein R^1 , R^2 and R^3 are each independently a hydrocarbon group having 1 to 10 carbon atoms, ~~with the proviso that X^1 and X^2 cannot be hydrogen atoms at the same time;~~ and

a compound represented by the following formula (2):



wherein R^4 is a trifluoromethyl group or hydrocarbon group having 1 to 10 carbon atoms, and three R^4 's may be the same or different, and

~~a compound represented by the following formula (4):~~



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~~wherein Y is a cyclopentadienyl, cyclohexadienyl, cycloheptadienyl, cyclooctadienyl, butadienyl or 2,3-dimethyl-1,3-butadienyl group, L is a carbonyl group, methyl group or ethenyl group, n is an integer of 1 to 4, and m is an integer of 0 to 2, with the proviso that n + m is 3 or 4, and two L's may be the same or different when m is 2.~~

Claim 2 (Currently Amended): A process for producing a metal ruthenium film ~~from~~ comprising applying the ruthenium compound of claim 1 by chemical vapor deposition.